

# Fangzhen Wu

## List of Publications by Year in descending order

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12  
papers

117  
citations

1478458

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1372553

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g-index

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docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Characterization of Threading Dislocations in PVT-Grown AlN Substrates via x-Ray Topography and Ray Tracing Simulation. <i>Journal of Electronic Materials</i> , 2014, 43, 838-842.	2.2	29
2	Simulation of Grazing-Incidence Synchrotron X-ray Topographic Images of Threading c+a Dislocations in 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1433, 53.	0.1	23
3	Analysis of Dislocation Behavior in Low Dislocation Density, PVT-Grown, Four-Inch Silicon Carbide Single Crystals. <i>Materials Research Society Symposia Proceedings</i> , 2010, 1246, 1.	0.1	18
4	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC Grown by PVT Method. <i>Journal of Electronic Materials</i> , 2016, 45, 2045-2050.	2.2	15
5	Grazing Incidence X-ray Topographic Studies of Threading Dislocations in Hydrothermal Grown ZnO Single Crystal Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2013, 1494, 121-126.	0.1	7
6	Synchrotron X-ray topographic study on nature of threading mixed dislocations in 4H-SiC crystals grown by PVT method. <i>Journal of Crystal Growth</i> , 2016, 452, 39-43.	1.5	6
7	Quantitative Comparison Between Dislocation Densities in Offcut 4H-SiC Wafers Measured Using Synchrotron X-ray Topography and Molten KOH Etching. <i>Journal of Electronic Materials</i> , 2013, 42, 794-798.	2.2	5
8	Characterization of V-shaped Defects in 4H-SiC Homoepitaxial Layers. <i>Journal of Electronic Materials</i> , 2015, 44, 1293-1299.	2.2	4
9	Characterization and Formation Mechanism of Six Pointed Star-Type Stacking Faults in 4H-SiC. <i>Journal of Electronic Materials</i> , 2013, 42, 787-793.	2.2	3
10	Direct Observation of Stacking Fault Nucleation from Deflected Threading Dislocations with Burgers Vector c+a in PVT Grown 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1693, 49.	0.1	3
11	A method to determine fault vectors in 4H-SiC from stacking sequences observed on high resolution transmission electron microscopy images. <i>Journal of Applied Physics</i> , 2014, 116, 104905.	2.5	2
12	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC c-Plane Wafers Grown by PVT Method. <i>ECS Transactions</i> , 2015, 69, 33-38.	0.5	1